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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/761,658	01/20/2004	Jiaw-Ren Shin	67,200-1194	3378
75	90 04/27/2005		EXAMINER	
TUNG & ASSOCIATES			DANG, PHUC T	
Suite 120 838 W. Long Lake Road		ART UNIT	PAPER NUMBER	
Bloomfield Hill			2818 DATE MAILED: 04/27/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)				
Office Action Commence	10/761,658	SHIN ET AL.				
Office Action Summary	Examiner	Art Unit				
	PHUC T. DANG	2818				
The MAILING DATE of this communication appears on the cover sheet with the correspondence address Period for Reply						
A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely. - If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication. - Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).						
Status						
1) Responsive to communication(s) filed on 20 Ja	nuary 2004.					
<i>;</i> —	This action is FINAL . 2b)⊠ This action is non-final.					
	Since this application is in condition for allowance except for formal matters, prosecution as to the ments is					
closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 45	3 O.G. 213.				
Disposition of Claims						
4) Claim(s) 1-20 is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. 5) Claim(s) is/are allowed. 6) Claim(s) 1-20 is/are rejected. 7) Claim(s) is/are objected to. 8) Claim(s) are subject to restriction and/or election requirement.						
Application Papers						
9) ☐ The specification is objected to by the Examiner. 10) ☑ The drawing(s) filed on 20 January 2004 is/are: a) ☑ accepted or b) ☐ objected to by the Examiner. Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a). Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d). 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.						
Priority under 35 U.S.C. § 119						
12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f). a) All b) Some * c) None of: 1. Certified copies of the priority documents have been received. 2. Certified copies of the priority documents have been received in Application No 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received.						
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date 012004.	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ate	O-152)			

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DETAILED ACTION

Election/Restrictions

1. Applicant's election with traverse filed on March 14, 2005 has been acknowledged.

The traverse is on the ground(s) that the Group I (claims 1-10) of the device can only made by the process contained in the Group II (claims 11-20) of the method invention. This is found persuasive. Therefore, the restriction filed on January 13, 2005 has been withdrawn.

2. Claims 1-20 are currently pending in the application.

Oath/Declaration

3. The oath/declaration filed on January 20, 2004 is acceptable.

Information Disclosure Statement

4. The office acknowledges receipt of the following items from the applicant:
Information Disclosure Statement (IDS) filed on January 20, 2004.

Specification

5. The specification has been checked to the extent necessary to determine the presence of all possible minor errors. However, the applicant's cooperation is requested in correcting any errors of which applicant may become aware in the specification.

Claim Rejections-35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the application regards as his invention.

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6. Claims 1-20 are rejected under 35 U.S.C. 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which the applicant regards as the invention.

In claims 1 and 11, a limitation of "a metal oxide semiconductor transistor of the second polarity formed within and upon the first doped well and a metal oxide semiconductor transistor of the first polarity formed within and upon the second doped well" is not clearly defined and pointed out distinctly the subject matter which is claimed as the Applicant's invention because the metal oxide semiconductor transistor of the second polarity and first polarity formed only upon, not within the first n doped well as shown in Figs. 4-5 of the specification.

In claims 6 and 16, a limitation of "a p metal oxide semiconductor transistor within and upon the first n doped well and a p metal oxide semiconductor transistor formed within and upon the first n doped well" is not clearly defined and pointed out distinctly the subject matter which is claimed as the Applicant's invention because the p metal oxide semiconductor transistor formed only upon, not within the first n doped well as shown in Figs. 4-5 of the specification. Corrections are required.

Allowable Subject Matter

7. Claims 1-20 would be allowable if rewritten or amended to overcome the rejection(s) under 35 U.S.C. 112 set forth in this Office action.

Conclusion

8. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Pan et al. (U.S. Patent No. 6,329,233 B1) discloses Method of manufacturing

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photodiode CMOS image sensor and Tung (U.S. patent No. 5,976,922) discloses Method for fabricating a high bias device compatible with a low device.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Phuc T. Dang whose telephone number is (571) 272-1776. The examiner can normally be reached on 8:00 am-5:00 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, 10. David C. Nelms can be reached on (571) 272-1787. The fax phone numbers for the organization where this application or proceeding is assigned are 703-872-9306 for regular communications and After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding 11. should be directed to the receptionist whose telephone number is 703-308-0956.

PD Langshur

Phuc T. Dang

Primary Examiner

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